



***FARJAMI & FARJAMI LLP***  
AN INTELLECTUAL PROPERTY LAW FIRM

www.farjami.com

RECEIVED  
CENTRAL FAX CENTER  
SEP 22 2004

26522 La Alameda Avenue, Suite 360  
Mission Viejo, California 92691  
tel: (949) 282-1000  
fax: (949) 282-1002

**FACSIMILE TRANSMISSION COVER SHEET**

**Date:** September 22, 2004

**To:** United States Patent and Trademark Office  
Examiner: Thien F. Tran; Art Unit: 2811

**Fax:** (703) 872-9306

**Re:** **Application Serial No.: 10/678,445**  
Filing Date: 10/3/2003; First Named Inventor: George Jonathan Kluth  
Attorney Docket No.: 0180146

**From:** Farjami & Farjami LLP

**Number of pages including the cover sheet:** 7

**Message:**

Enclosed please find the Amendment and Response to the Office Action dated September 10, 2004.

Thank you.

The documents accompanying this facsimile contain **PRIVILEGED AND CONFIDENTIAL** information intended only for use of the individual or entity named above. If you are not the intended recipient, disclosure, copying, distribution or use of the contents of this facsimile information is prohibited. If you have received this facsimile in error, please immediately notify us by telephone and return the original facsimile to us at the above address via U.S. Postal Service. We will reimburse you for all expenses incurred.

Attorney Docket No.: 0180146

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**RECEIVED  
CENTRAL FAX CENTER  
SEP 22 2004**

In re Application of: Kluth, et al.

Art Unit: 2811

Serial No.: 10/678,445

Examiner: Tran, Thien F.

Filed: October 3, 2003

**For: Method for Forming Polysilicon Gate  
On High-K Dielectric and Related  
Structure**

**AMENDMENT AND RESPONSE TO OFFICE ACTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the Office Action dated September 10, 2004 in the above-referenced patent application. Please enter and consider the following amendments and remarks.